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Kind regards,

Team Nexperia



PBSS306NX

100 V, 4.5 A NPN low V_{CEsat} (BISS) transistor Rev. 02 — 8 December 2009

Product data sheet

Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS306PX.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	4.5	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	9	Α
R _{CEsat}	collector-emitter saturation resistance	$I_C = 4 A;$ $I_B = 200 \text{ mA}$	[1] -	40	56	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



2. Pinning information

Table 2. Pinning

	9		
Pin	Description	Simplified outline	Symbol
1	emitter		_
2	collector		2
3	base	3 2 1	3 ————————————————————————————————————

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS306NX	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBSS306NX	*5G

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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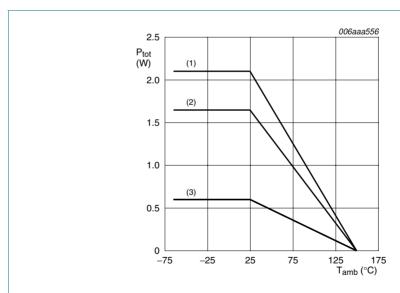
Limiting values 5.

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		• •	,		
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	100	V
V_{CEO}	collector-emitter voltage	open base	-	100	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current		-	4.5	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	9	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	0.6	W
			[2] _	1.65	W
			[3] _	2.1	W
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- FR4 PCB, standard footprint

Power derating curves Fig 1.

Product data sheet

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1]	-	-	208	K/W
			[2]	-	-	76	K/W
			[3]	-	-	60	K/W
$R_{th(j\text{-sp})}$	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

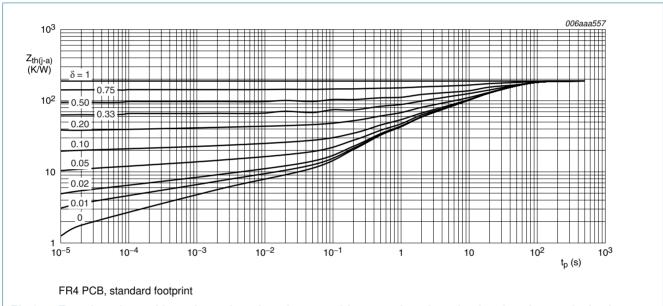
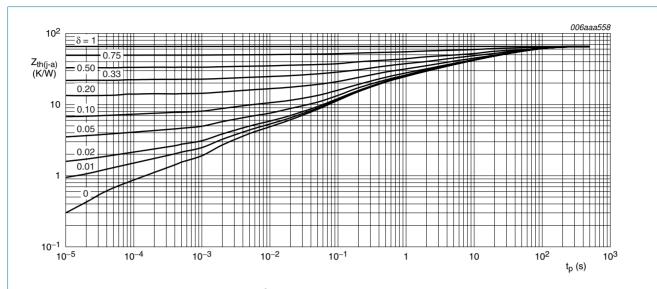
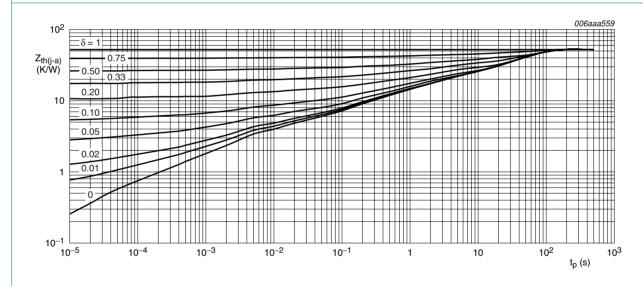


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



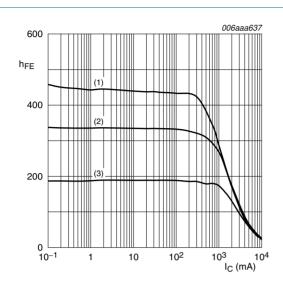
Characteristics

Table 7. Characteristics

T_{amb} = 25 °C unless otherwise specified.

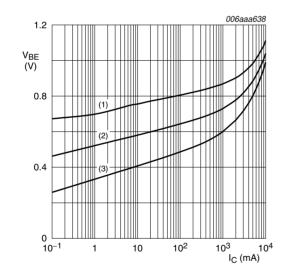
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 80 \text{ V}; I_{E} = 0 \text{ A}$	-	-	100	nΑ
	current	$V_{CB} = 80 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 2 \text{ V}; I_{C} = 0.5 \text{ A}$	<u>[1]</u> 200	330	-	
		V _{CE} = 2 V; I _C = 1 A	<u>11</u> 150	270	-	
		V _{CE} = 2 V; I _C = 2 A	100	175	-	
		$V_{CE} = 2 \text{ V}; I_{C} = 4 \text{ A}$	<u>[1]</u> 50	85	-	
		$V_{CE} = 2 \text{ V}; I_{C} = 5 \text{ A}$	<u>[1]</u> 40	70	-	
V _{CEsat}	V _{CEsat} collector-emitter saturation voltage	$I_C = 0.5 A$; $I_B = 50 mA$	<u>[1]</u> -	27	40	mV
		$I_C = 1 A$; $I_B = 50 \text{ mA}$	<u>[1]</u> -	53	75	mV
		$I_C = 1 A; I_B = 10 \text{ mA}$	<u>[1]</u> -	100	150	mV
		$I_C = 2 A$; $I_B = 40 \text{ mA}$	<u>[1]</u> -	115	160	mV
		$I_C = 4 A$; $I_B = 200 \text{ mA}$	<u>[1]</u> -	160	225	mV
		$I_C = 4 A$; $I_B = 400 \text{ mA}$	<u>[1]</u> -	140	200	mV
		$I_C = 4.5 \text{ A}; I_B = 225 \text{ mA}$	<u>[1]</u> -	170	245	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = 4 A$; $I_B = 200 mA$	[1] -	40	56	mΩ
V _{BEsat}	base-emitter saturation	$I_C = 1 A; I_B = 100 \text{ mA}$	<u>[1]</u> -	0.81	0.9	V
	voltage	$I_C = 4 \text{ A}; I_B = 400 \text{ mA}$	<u>[1]</u> -	0.94	1.05	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}$	[1] -	0.78	0.85	V
t _d	delay time	$V_{CC} = 12.5 \text{ V}; I_C = 3 \text{ A};$	-	15	-	ns
t _r	rise time	[−] I _{Bon} = 0.15 A; − I _{Boff} = −0.15 A	-	315	-	ns
t _{on}	turn-on time	- 180⊞0.13 A	-	330	-	ns
t _s	storage time		-	240	-	ns
t _f	fall time		-	290	-	ns
t _{off}	turn-off time		-	530	-	ns
f _T	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 100 \text{ mA};$ f = 100 MHz	-	110	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	23	40	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$



- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

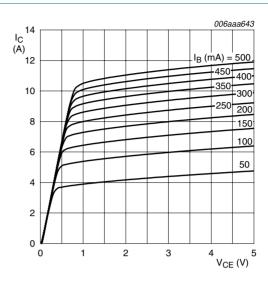
Fig 5. DC current gain as a function of collector current; typical values





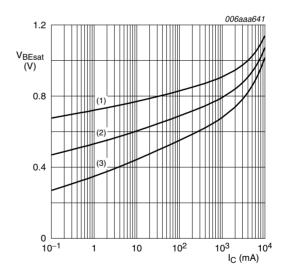
- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Base-emitter voltage as a function of collector current; typical values



T_{amb} = 25 °C

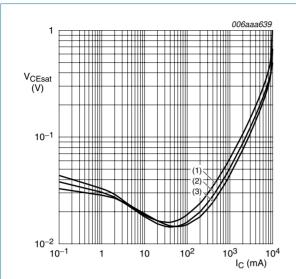
Fig 6. Collector current as a function of collector-emitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



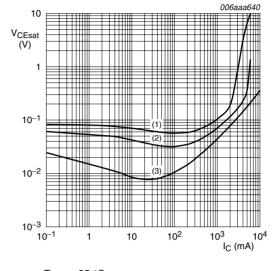
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values

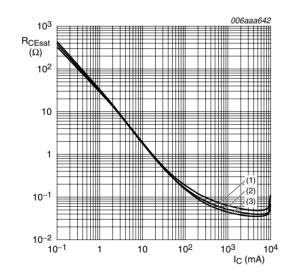


(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



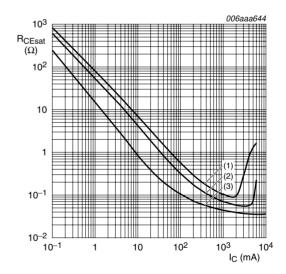
$$I_{C}/I_{B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

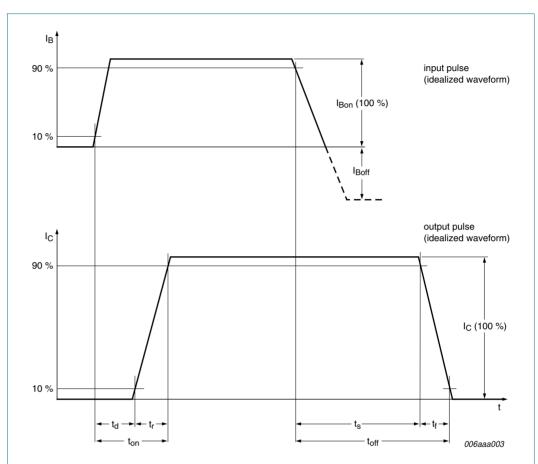


Fig 13. BISS transistor switching time definition

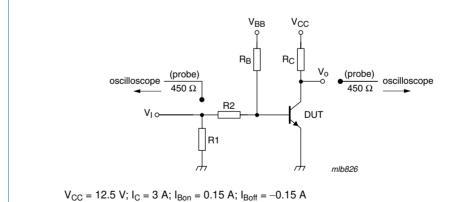
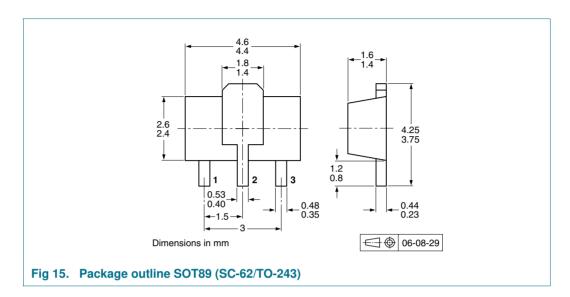


Fig 14. Test circuit for switching times

9. Package outline



10. Packing information

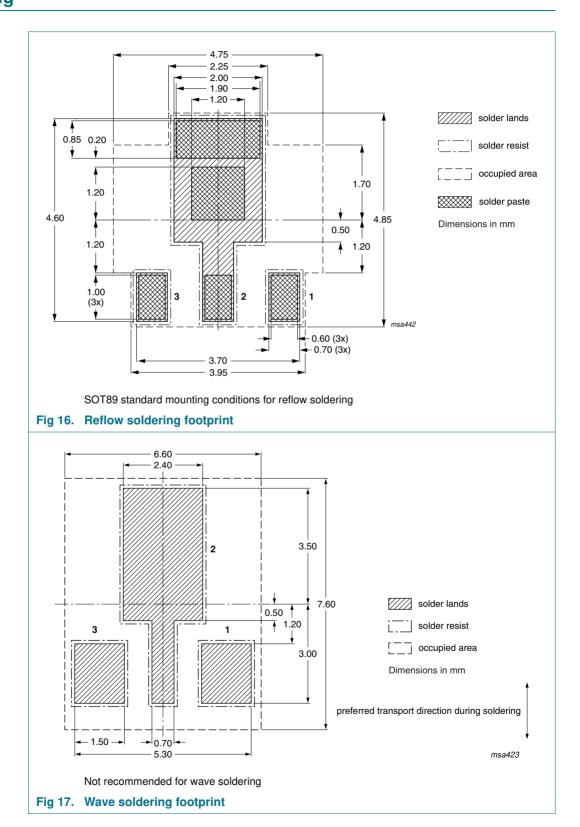
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			1000	4000
PBSS306NX	SOT89	8 mm pitch, 12 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see Section 15.

11. Soldering

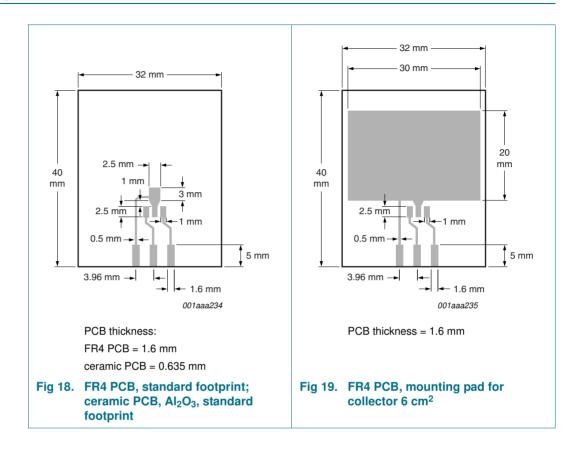


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100 V, 4.5 A NPN low V_{CEsat} (BISS) transistor

12. Mounting

Product data sheet





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100 V, 4.5 A NPN low V_{CEsat} (BISS) transistor

13. Revision history

Table 9. **Revision history**

Product data sheet

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS306NX_2	20091208	Product data sheet	-	PBSS306NX_1
Modifications:		neet was changed to reflect w legal definitions and disc		
	 Figure 15 "F 	Package outline SOT89 (SC	-62/TO-243)": updated	
	 Figure 16 "F 	Reflow soldering footprint": I	updated	
	• Figure 17 "V	Nave soldering footprint": up	odated	
PBSS306NX_1	20060821	Product data sheet	-	-

PBSS306NX

100 V, 4.5 A NPN low V_{CEsat} (BISS) transistor

14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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